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BATOP optoelectronics

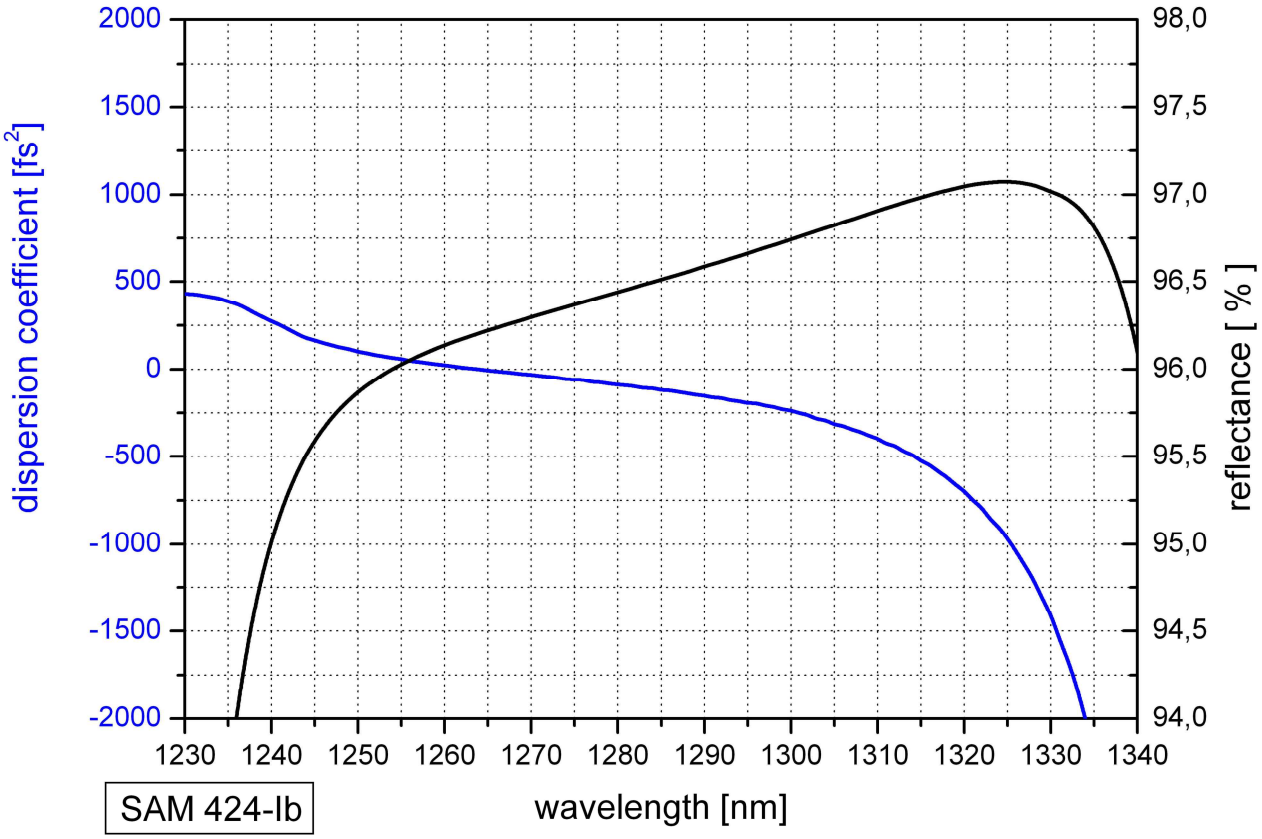
SAM™ Data Sheet SAM-1300-4-10ps-x, λ = 1300 nm

Laser wavelength	λ = 1300 nm
High reflection band	λ = 1240 .. 1340 nm
Saturable absorptance	A_0 = 4 %
Saturation fluence	Φ_{sat} = 70 µJ/cm^2
Relaxation time constant	τ ≤ 10 ps
Modulation depth	ΔR = 2.5 %
Damage threshold	Φ = 3 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance and dispersion coefficient D_2



Group Delay Dispersion (GDD)

Dispersion coefficient $D_2(\omega) = \frac{\partial^2 \varphi}{\partial \omega^2}$ with φ - reflected phase

$\omega = 2\pi \frac{c}{\lambda}$ - angular frequency